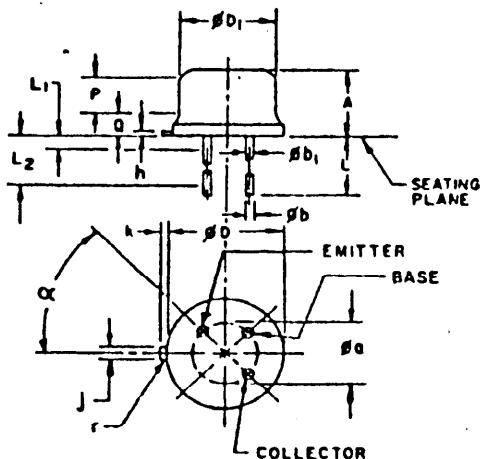


21 August 1972

## MILITARY SPECIFICATION

SEMICONDUCTOR DEVICE, TRANSISTOR, PNP, SILICON  
TYPE 2NI234

Add attached figure 1 to MIL-S-19500/179A(EL):



LTR	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN	MAX	MIN	MAX	
A	.240	.260	6.10	6.60	
B1	.200	TP	5.08	TP	6
Bb	.016	.021	.41	.53	7,8
Bb1	.016	.019	.41	.48	7,8
B1	.335	.370	8.51	9.40	
Bb1	.305	.335	7.75	8.51	
h	.009	.011	.23	1.04	
r	.034	.045	.71	.86	2
k	.024	.045	.74	1.14	3
I	1.500	1.750	38.10	44.45	7,8
L1	---	.050	---	1.27	7,8
L2	.250	---	6.35	---	7,8
L3	.100	---	2.54	---	5
Q	---	.050	---	1.27	4
r	---	.010	---	.25	9
alpha	45	TP	45	TP	6

## NOTES:

- Metric equivalents (to the nearest .01 mm) are given for general information only and are based upon 1 inch = 25.4 mm.
- Beyond r(radius) maximum, J shall be held for a minimum length of .011(.28 mm).
- k measured from maximum  $\phi D$ .
- Outline in this zone is not controlled.
- $\phi D_1$  shall not vary more than .010(.25 mm) in zone P. This zone is controlled for automatic handling.
- Leads at gage plane .054 + .001-.000(1.37+.03-.00 mm) below seating plane shall be within .007(.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. The device may be measured by direct methods or by the gage and gaging procedure shown in figure 2.
- $\phi b_1$  applies between L1 and L2.  $\phi b$  applies between L2 and L minimum. Diameter is uncontrolled in L1 and beyond L minimum.
- All three leads.
- r(radius) applies to both inside corners of tab.

FIGURE 1. Physical dimensions of transistor type 2NI234 (TO-5).

Custodian:  
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